

NPN TRANSISTORS



TO-92/TO-226AA

'2N' and 'TP' DEVICE TYPES

ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$

Device Type	I_C Max. (mA)	$V_{(BR)CBO}$ (V)	$V_{(BR)CEO}$ (V)	$V_{(BR)EBO}$ (V)	I_{CBO}		DC Current Gain				$V_{CE(sat)}$		f_T		C_{ob}^1 (pF)	t_s^1 (ns)	NF ¹ (dB)	Pinning 1, 2, 3
					Max. (nA)	@ V_{CB} (V)	h_{FE}	h_{FE}	@ I_C (mA)	@ V_{CE} (V)	Max. (V)	@ I_C (mA)	Min. (MHz)	@ I_C (mA)				
TP2222A	500	75	40	6.0	10	60	100	300	150	10	0.3	150	250	20	8.0	225	—	EBC
2N3416	500	50	50	5.0	100	50	75	225	2.0	4.5	0.3	50	—	—	—	—	—	ECB
2N3417	500	50	50	5.0	100	50	180	540	2.0	4.5	0.3	50	—	—	—	—	—	ECB
2N3904	200	60	40	6.0	50	30	100	300	10	1.0	0.2	10	300	10	4.0	—	5.0	EBC
2N4401	500	60	40	6.0	100	30	100	300	150	1.0	0.4	150	250	20	6.5	225	—	EBC
2N5088	100	35	30	—	50	20	300	900	0.1	5.0	0.5	10	—	—	4.0	—	3.0	EBC
2N5308	500	40	40	12	100	40	7k	70k	2.0	5.0	1.4	200	60	2.0	10	—	—	ECB
2N6427	500	40	40	12	50	30	10k	100k	10	5.0	1.2	50	130	10	7.0	—	10	EBC

NOTES: 1) Maximum at typical JEDEC conditions.

2) $V_{(BR)CES}$

'MPS' DEVICE TYPES

ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$

Device Type	I_C Max. (mA)	$V_{(BR)CBO}$ (V)	$V_{(BR)CEO}$ (V)	$V_{(BR)EBO}$ (V)	I_{CBO}		DC Current Gain				$V_{CE(sat)}$		f_T		C_{ob}^1 (pF)	t_s^1 (ns)	NF ¹ (dB)	Pinning 1, 2, 3
					Max. (nA)	@ V_{CB} (V)	h_{FE}	h_{FE}	@ I_C (mA)	@ V_{CE} (V)	Max. (V)	@ I_C (mA)	Min. (MHz)	@ I_C (mA)				
MPSA06	800	80	80	4.0	100	80	50	—	100	1.0	0.25	100	100	10	—	—	—	EBC
MPSA13	500	30 ²	—	10	100	30	10k	—	100	5.0	1.5	100	125	10	—	—	—	EBC
MPSA14	500	30 ²	—	10	100	30	20k	—	100	5.0	1.5	100	125	10	—	—	—	EBC
MPSA42	500	300	300	6.0	100	200	40	—	30	10	0.5	20	50	10	3.0	—	—	EBC

NOTES: 1) Maximum at typical JEDEC conditions.

2) $V_{(BR)CES}$